

- Conclusions from I/p-D/p characters.
  - D Par Iss to be current from mosfet, then Vinj = Vinz
  - @ If Vin 1 1 than Vinz, M1 carries greater current than M2. Hence Vonta drops below Vouta
  - @ Et Won 1 03 very large, them M203 off, hence Vouts = Vob-IssRD (Mino/P) Vout = > Vob (Max o/P)
  - O Small signal gain us maximum for Vin1 = Vin2 The small eigenal gain (1) if Ving-Vina 1

So, have a commun mode behaviour, ive connect Vins and Vinz to a shyle source called Vin, cm

case 1: Vin, cm =0, both M, and M, are off. :: IDs =0 making Ip, = ID2 =0

ξ R<sub>o</sub> V02 NI (Vb - TLynz)

tence, M3 can be replaced with resistor Ron, since Msisin deep triode region

case 2: Vin, cm becomes more positive.

- · both: H, and M2 turns on, i'f Vin, cm > Vth. Then later In and In. (1)
- hence Vp 1 · For a significant high Vin, cm, the Vos of M3 exceeds vgs 2 - Vth3, thus allowing it to operate in saturation?
- · Hence, for poper operation, 2 Vgs1 + (vgs3-V443)

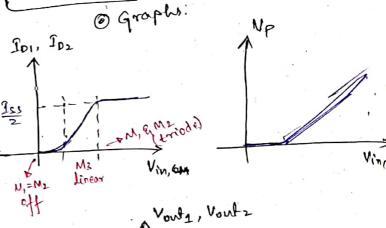
cases: What if Vin, con Further 1) · M, Q M, enters triode region. if

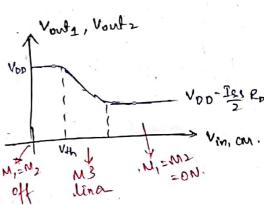
Vincom > Vowt + Vth Vinim > VDD - Roles + Vth

· This sels restricts the maximum Vinan to be ruinimum value DIO. [VDD-ROPES, VDD]

conclusion & formulae

Vgsit (Vgsz VHz) Vin, cu = min [Von-Ro Iss + V+h





- Small-signal differential gain of D.P.

